AMENDMENTS TO THE SPECIFICATION

On page 1, kindly amend the title as follows:

DIFFUSION REPLICA DELAY CIRCUIT <u>METHOD</u>

On page 1, after the heading CROSS-REFERENCE TO RELATED APPLICATION (S),

kindly amend the paragraph added in the Preliminary Amendment regarding U.S. Application

No. 09/776,029 as follows:

This is a continuation of U.S. Application No. 09/776,029, entitled "Diffusion Replica

Delay Circuit," filed February 2, 2001 in the names of Esin Terzioglu et al.<u>, now U.S. Patent No.</u>

<u>6,611,465.</u>

On pages 4-5, kindly delete the present SUMMARY OF THE INVENTION, and

substitute the following new SUMMARY OF THE INVENTION:

SUMMARY OF THE INVENTION

The invention is useful in a memory component including a dummy cell with a dummy bit
line and a plurality of wordlines, the memory component having a memory component capacitance
and memory component operational characteristics, including dummy bitline capacitance of the
dummy bitline. In such an environment, a diffusion replica delay circuit can be implemented by a
method comprising:

  a. coupling a diffusion replica capacitor to the dummy bit line and one wordline of the
      plurality of wordlines, coupling the diffusion replica capacitor to the memory
      component, storing in the diffusion replica capacitor a predetermined replica charge
      representative of the dummy bitline capacitance, and matching the diffusion replica
      capacitance of the diffusion replica capacitor to the dummy bitline capacitance, and

  b. coupling a diffusion replica transistor with the diffusion replica capacitor, and
      coupling the diffusion replica transistor between the diffusion replica capacitor and a
      charge sink, the transistor being disposed to control the magnitude of the
      predetermined replica charge.